

AMENDMENTS TO THE SPECIFICATION:

Please cancel the paragraph on page 14, line 23, through page 15, line 12, and replace with the following paragraph:

Second heat dissipator 12 is joined to the back side of heat sink 9 with first ~~silicon~~ silicone sheet 11 interposed. First ~~silicon~~ silicone sheet 11 has a stress-absorbing property (elasticity) for absorbing the stress caused by the relative expansion and contraction between first heat dissipator 9 and second heat dissipator 12 and a heat-transfer property for transmitting the heat of first heat dissipator 9 to second heat dissipator 12; and ~~silicon~~ silicone is used due its superior buffer effect. Second heat dissipator 12 includes an extensive second heat dissipator surface 13 as its exterior surface. Spacers 14 are interposed between wiring substrate 2 and second heat dissipator 12. Spacers 14 may be formed as a single unit with second heat dissipator 12. Second heat dissipator 12 is secured to wiring substrate 2 by first securing screws 15.

Please cancel the paragraph on page 15, lines 13-23, and replace with the following paragraph:

Third heat dissipator 17 is joined to the front surface of semiconductor chip mounting substrate 1 with second ~~silicon~~ silicone sheet 16 interposed. Second ~~silicon~~ silicone sheet 16 has a stress-absorbing property for absorbing the stress caused by the relative expansion and contraction between semiconductor chip mounting substrate 1 and third heat dissipator 17 and a heat-transfer property for transmitting the heat of semiconductor chip mounting

substrate 1 to third heat dissipator 17. Third heat dissipator 17 is secured to wiring substrate 2 by second securing screws 18.

Please cancel the paragraph on page 17, lines 2-17, and replace with the following paragraph:

The first heat-dissipating structure is made up by: semiconductor chip mounting substrate 1, a plurality of semiconductor chips 7, and first heat dissipator 9, semiconductor chip mounting substrate 1 being incorporated inside the first heat-dissipating structure. The second heat-dissipating structure is made up by wiring substrate 2, second heat dissipator 12, and third heat dissipator 17, wiring substrate 2 being incorporated inside the second heat-dissipating structure. The heat that is generated by the first heat-dissipating structure is conveyed to second heat dissipator 12 and third heat dissipator 17 by way of first ~~silicon~~ silicone sheet 11 and second ~~silicon~~ silicone sheet 16, and then discharged into the exterior atmosphere by way of the extensive second heat-dissipating surface 13 of second heat dissipator 12 and the extensive heat-dissipating surface of third heat dissipator 17.

Please cancel the paragraph on page 17, line 18, through page 18, line 5, and replace with the following paragraph:

The heat that is transmitted to second heat dissipator 12 generates thermal stress in second heat dissipator 12, and as a counter-reaction, there is a potential for this thermal stress to be transmitted to side portions 21. However, this thermal stress is effectively absorbed by first ~~silicon~~ silicone sheet 11, which has a buffer effect, and the transmission of thermal stress

by way of side portions 21 to semiconductor chip mounting substrate 1 is therefore suppressed. The thermal stress that is generated in second heat dissipator 12 is transmitted by way of spacers 14 to wiring substrate 2, but this thermal stress is absorbed in wiring substrate 2, whereby the concern for thermal stress being transmitted to semiconductor chips 7 is virtually eliminated.

Please cancel the paragraph on page 18, lines 6-15, and replace with the following paragraph:

The thermal stress that is generated in third heat dissipator 17 is effectively absorbed by second ~~silicon~~ silicone sheet 16, and the transmission of this thermal stress to semiconductor chip mounting surface 1 is effectively suppressed. Semiconductor chips 7 are thus incorporated inside the first heat-dissipating structure in a floating state with respect to thermal stress, and the first heat-dissipating structure is incorporated inside the second heat-dissipating structure in a floating state with respect to thermal stress.

Please cancel the paragraph on page 20, lines 10-20, and replace with the following paragraph:

The thermal and mechanical joining relationship between semiconductor chips 7 and first heat dissipator 9, the thermal and mechanical joining relationship between first heat dissipator 9 and second heat dissipator 12 by way of first ~~silicon~~ silicone sheet 11, and the thermal and mechanical joining relationship between wiring substrate 2 and second heat dissipator 12 by way of spacers 14 are each identical to the thermal and mechanical joining

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relationships of the previously described embodiment. Third heat dissipator 17 of the previously described embodiment has been omitted in this embodiment.